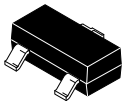
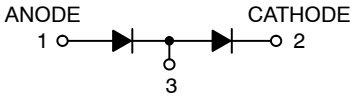
# Dual Series Switching Diode

# BAV99L, SBAV99L



CASE 318
SOT–23
STYLE 11




### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS (Each Diode)

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Reverse Voltage | $V_R$ | 100 | Vdc |
| Forward Current | $I_F$ | 215 | mAdc |
| Peak Forward Surge Current | $I_{FM(surge)}$ | 500 | mAdc |
| Repetitive Peak Reverse Voltage | $V_{RRM}$ | 100 | V |
| Average Rectified Forward Current (Note 1) (averaged over any 20 ms period) | $I_{F(AV)}$ | 715 | mA |
| Repetitive Peak Forward Current | $I_{FRM}$ | 450 | mA |
| Non–Repetitive Peak Forward Current<br>t = 1.0 μs<br>t = 1.0 ms<br>t = 1.0 s | $I_{FSM}$ | <br>2.0<br>1.0<br>0.5 | A |

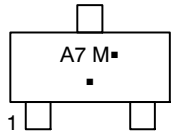
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|---|---|---|
| Total Device Dissipation<br>FR–5 Board (Note 1) $T_A$ = 25°C<br>Derate above 25°C | $P_D$ | 225<br><br>1.8 | mW<br><br>mW/°C |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 556 | °C/W |
| Total Device Dissipation<br>Alumina Substrate (Note 2)<br>$T_A$ = 25°C<br>Derate above 25°C | $P_D$ | 300<br><br><br>2.4 | mW<br><br><br>mW/°C |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 417 | °C/W |
| Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | –65 to +150 | °C |

1. FR–5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in 99.5% alumina.

### MARKING DIAGRAM




A7 = Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| BAV99LT1G | SOT–23 (Pb–Free) | 3,000 / Tape & Reel |
| SBAV99LT1G | SOT–23 (Pb–Free) | 3,000 / Tape & Reel |
| BAV99LT3G | SOT–23 (Pb–Free) | 10,000 / Tape & Reel |
| SBAV99LT3G | SOT–23 (Pb–Free) | 10,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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**OFF CHARACTERISTICS** ($T_A$ = 25°C unless otherwise noted) (Each Diode)

| Characteristic | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| Reverse Breakdown Voltage,<br>($I_{(BR)}$ = 100 μA) | $V_{(BR)}$ | 100 | – | Vdc |
| Reverse Voltage Leakage Current,<br>($V_R$ = 100 Vdc)<br>($V_R$ = 25 Vdc, $T_J$ = 150°C)<br>($V_R$ = 70 Vdc, $T_J$ = 150°C) | $I_R$ | –<br>–<br>– | 1.0<br>30<br>50 | μAdc |
| Diode Capacitance,<br>($V_R$ = 0, f = 1.0 MHz) | $C_D$ | – | 1.5 | pF |
| Forward Voltage,<br>($I_F$ = 1.0 mAdc)<br>($I_F$ = 10 mAdc)<br>($I_F$ = 50 mAdc)<br>($I_F$ = 150 mAdc) | $V_F$ | –<br>–<br>–<br>– | 715<br>855<br>1000<br>1250 | mVdc |
| Reverse Recovery Time,<br>($I_F$ = $I_R$ = 10 mAdc, $i_{R(REC)}$ = 1.0 mAdc) $R_L$ = 100 Ω | $t_{rr}$ | – | 6.0 | ns |
| Forward Recovery Voltage,<br>($I_F$ = 10 mA, $t_r$ = 20 ns) | $V_{FR}$ | – | 1.75 | V |

## CURVES APPLICABLE TO EACH DIODE

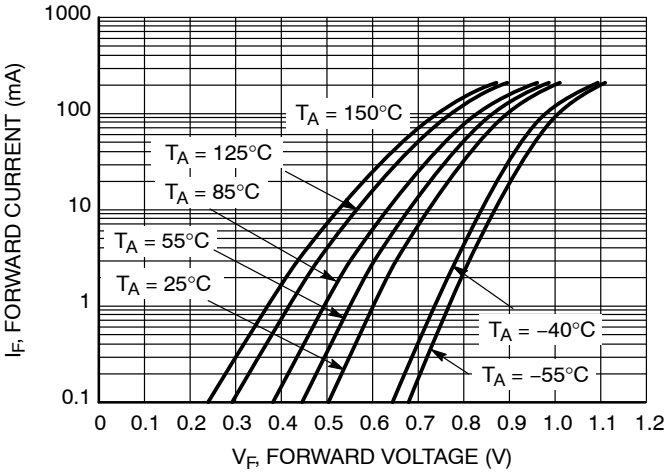



**Figure 1. Forward Voltage**

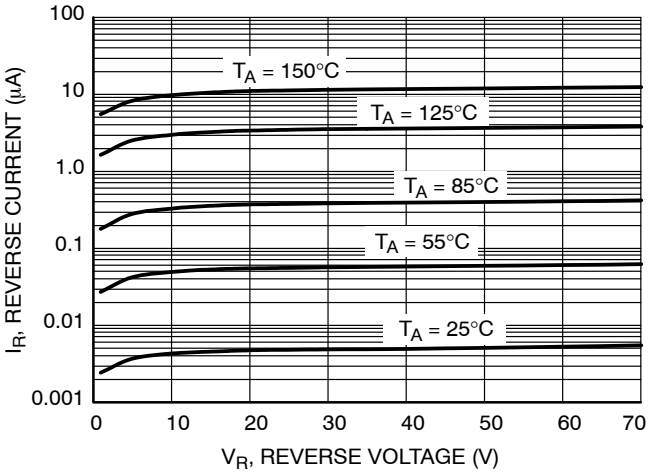



**Figure 2. Leakage Current**

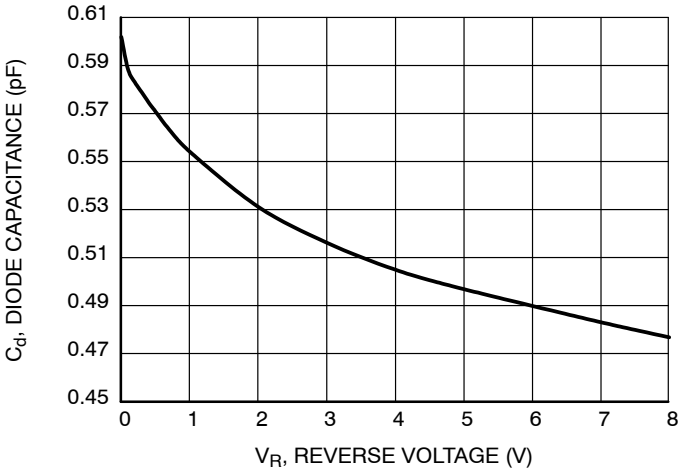
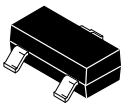


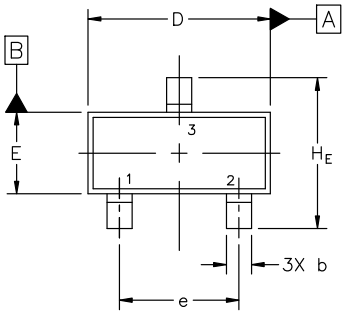

**Figure 3. Capacitance**



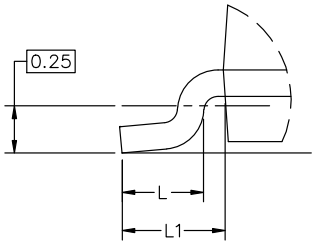
SCALE 4:1

**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**
CASE 318
ISSUE AU

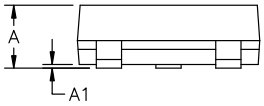
DATE 14 AUG 2024



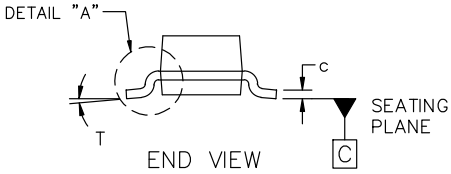

TOP VIEW




DETAIL "A"
Scale 3:1




SIDE VIEW

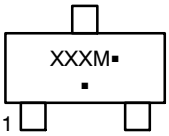



END VIEW

| MILLIMETERS | | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 |
| A1 | 0.01 | 0.06 | 0.10 |
| b | 0.37 | 0.44 | 0.50 |
| c | 0.08 | 0.14 | 0.20 |
| D | 2.80 | 2.90 | 3.04 |
| E | 1.20 | 1.30 | 1.40 |
| e | 1.78 | 1.90 | 2.04 |
| L | 0.30 | 0.43 | 0.55 |
| L1 | 0.35 | 0.54 | 0.69 |
| $H_E$ | 2.10 | 2.40 | 2.64 |
| T | 0° | −−− | 10° |

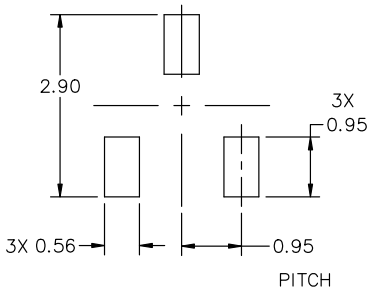
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

**GENERIC MARKING DIAGRAM***




XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.




RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

| | | |
|---|---|---|
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| **DESCRIPTION:** | **SOT−23 (TO−236) 2.90x1.30x1.00 1.90P** | **PAGE 1 OF 2** |

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**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE




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